Schottky Barrier Diode

Features

1. High reliability
2. Low reverse current and low forward voltage

Applications

Low current rectification and high speed switching

Construction

Silicon epitaxial planar

Absolute Maximum Ratings

T_j=25℃

Parameter	Test Conditions	Type	Symbol	Value	Unit
Repetitive peak reverse voltage		1N60	V_{RRM}	40	V
		1N60P	V_{RRM}	45	V
Peak forward surge current	t_p≦1 s	1N60	I_{FSM}	150	mA
		1N60P	I_{FSM}	500	mA
Forward continuous current	T_a=25℃	1N60	I_F	30	mA
		1N60P	I_F	50	mA
Storage temperature range			T_{stg}	-65~+125	℃

Maximum Thermal Resistance

T_j=25℃

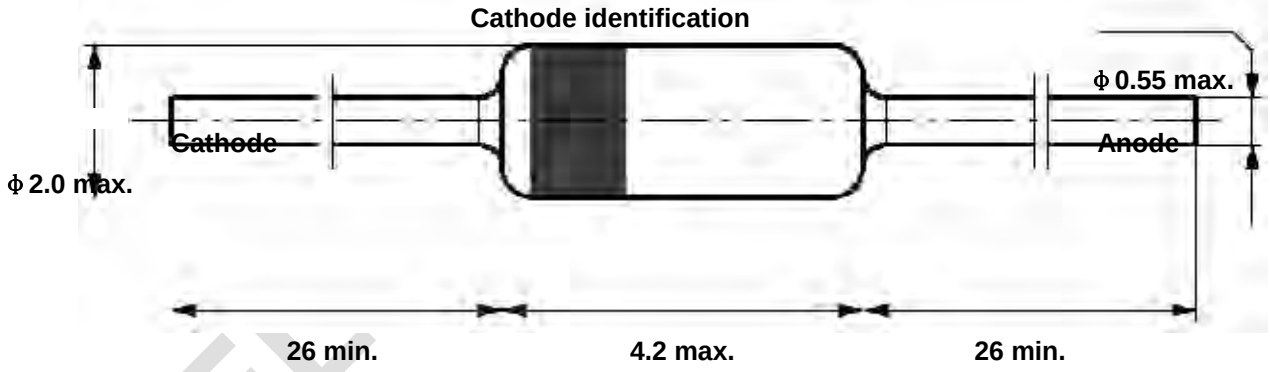
Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	on PC board 50mm×50mm×1.6mm	R_{thJA}	250	K/W

Electrical Characteristics

T_j=25℃

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=1mA	1N60	V_F		0.32	0.5	V
		1N60P	V_F		0.24	0.5	V
	I_F=30mA	1N60	V_F		0.65	1.0	V
	I_F=200mA	1N60P	V_F		0.65	1.0	V
Reverse current	V_R=15V	1N60	I_R		0.1	0.5	μA
		1N60P	I_R		0.5	1.0	μA
Junction capacitance	V_R=1V, f=1MHz	1N60	C_J		2.0		pF
	V_R=10V, f=1MHz	1N60P	C_J		6.0		pF
Reverse recovery time	I_F=I_R=1mA I_{rr}=1mA R_C=100		t_{rr}			1.0	ns

Dimensions in mm



Standard Glass Case
JEDEC DO 35